

RM4 - RM4Z

PRV : 100 - 400 Volts
Io : 1.7 Ampere

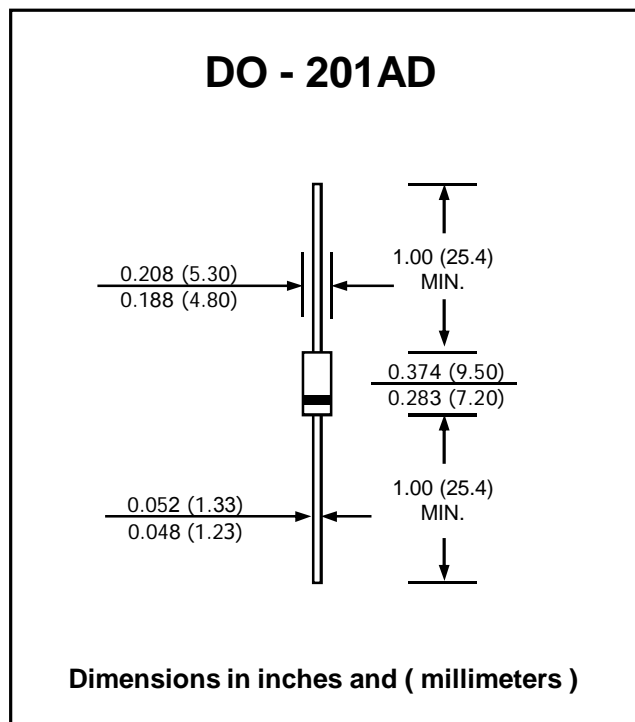
FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : DO-201AD Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 1.21 grams

SILICON RECTIFIER DIODES



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	RM4Y	RM4Z	RM4	UNIT
Maximum Reverse Voltage	V_{RM}	100	200	400	V
Maximum Peak Reverse Surge Voltage	V_{RSM}	150	250	450	V
Maximum Average Forward Current	$I_{F(AV)}$	1.7 (3.0 A is with Heatsink)			A
Maximum Peak Forward Surge Current Half-cycle Sine wave, 50 Hz, Single Shot	I_{FSM}	200			A
Maximum Forward Voltage at $I_F = 3.0$ A	V_F	0.95			V
Maximum Reverse Current at $V_R = V_{Rmax}$	I_R	10			μA
	$I_{R(H)}$	50			μA
Junction Temperature Range	T_J	- 40 to + 150			°C
Storage Temperature Range	T_{STG}	- 40 to + 150			°C

RATING AND CHARACTERISTIC CURVES (RM4 - RM4Z)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

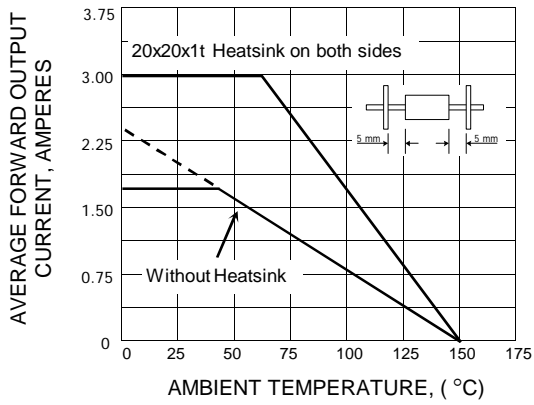


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

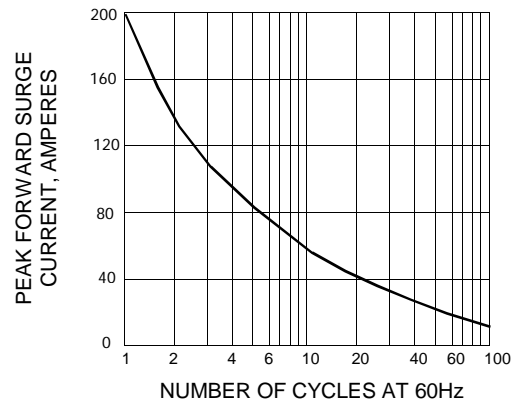


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

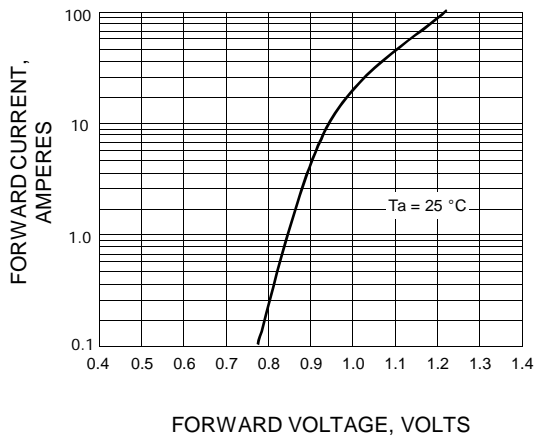


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

